

GaAs High Isolation Switch DC - 3.0 GHz

**MASWSS0169
V2**

Features

- Low Power Consumption: < 20 μ A @ +3 V
- High Isolation: 50 dB Typical @ 2 GHz
- Low Insertion Loss: 0.7 dB @ 2 GHz
- Positive 2.5 to 5 V Control
- Lead-Free MSOP-10 Package
- 100% Matte Tin Plating over Copper
- Halogen-Free "Green" Mold Compound
- 260°C Reflow Compatible
- RoHS* Compliant Version of SW-439

Description

M/A-COM's MASWSS0169 is a GaAs MMIC SPDT switch in a lead-free MSOP-10 surface mount plastic package. This part is ideal for high isolation, broadband switching requirements. Typical applications include synthesizer switching, transmit/receive switching, switch matrices and filter banks in systems such as radio and cellular equipment, PCM, GPS, and fiber optic modules.

The MASWSS0169 is fabricated as a monolithic GaAs MMIC using a 0.5 micron PHEMT process. The process features full passivation.

Ordering Information

Part Number	Package
MASWSS0169	Bulk Packaging
MASWSS0169TR-3000	3000 piece reel
MASWSS0169SMB	Sample Board

Note: Reference Application Note M513 for reel size information.

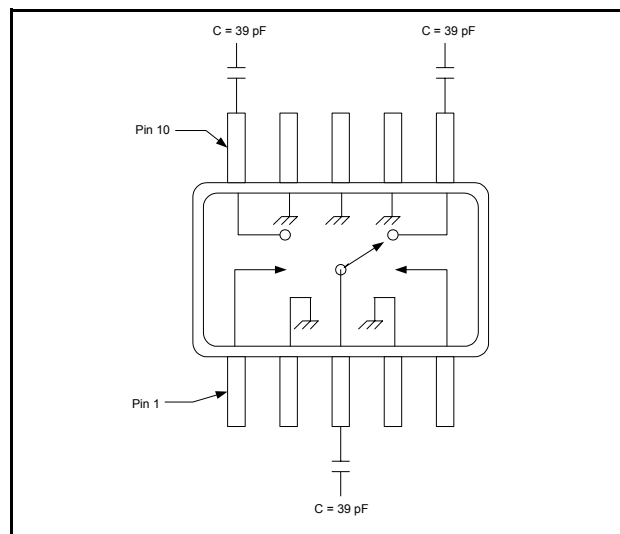
Absolute Maximum Ratings^{1,2}

Parameter	Absolute Maximum
Input Power	+30 dBm
Operating Voltage	+8.5 Volts
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

1. Exceeding any one or combination of these limits may cause permanent damage to this device.
2. M/A-COM does not recommend sustained operation near these survivability limits.

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

Functional Schematic³



3. For improved performance at frequencies below 500 MHz, use larger value capacitors.

Pin Configuration

Pin No.	Function	Pin No.	Function
1	Control 1	6	RF Port 2
2	Ground	7	Ground
3	RF Input	8	Ground
4	Ground	9	Ground
5	Control 2	10	RF Port 1

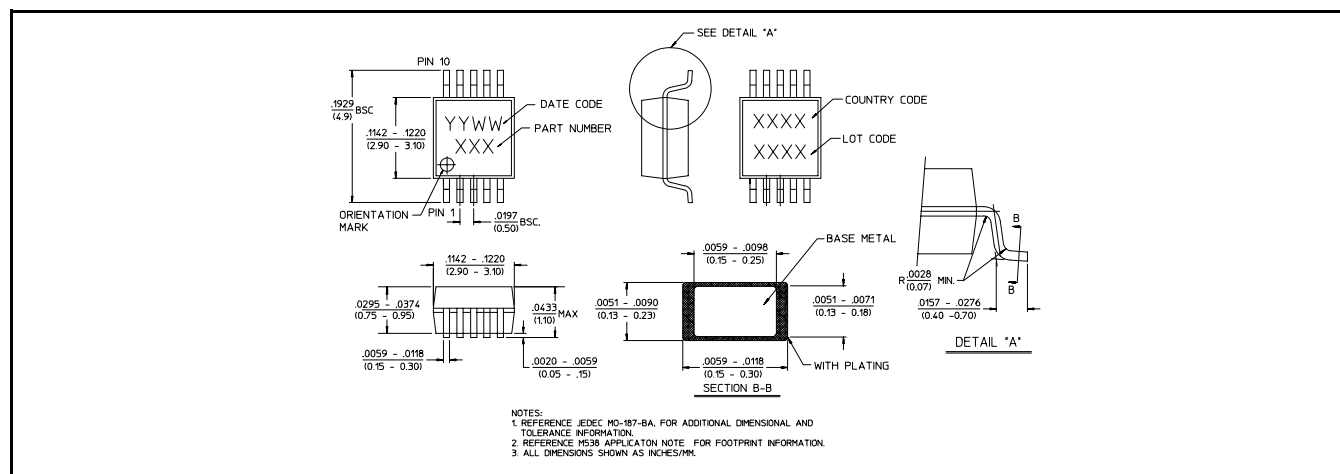
Truth Table^{4,5}

Control V1	Control V2	RFC - RF1	RFC - RF2
0	1	Off	On
1	0	On	Off

4. External DC blocking capacitors are required on all RF ports.
5. "0" = 0 ± 0.2 Vdc, "1" = +2.5 to +5 Vdc

**GaAs High Isolation Switch
DC - 3.0 GHz**
**MASWSS0169
V2**
Electrical Specifications: $T_A = 25^\circ\text{C}$, $V_C = 0 / 3 \text{ V}$, $Z_0 = 50\Omega$

Parameter	Test Conditions	Units	Min	Typ	Max
Insertion Loss	500 MHz - 1.0 GHz	dB	—	0.55	0.65
	1.0 - 2.0 GHz	dB	—	0.65	—
	2.0 - 3.0 GHz	dB	—	0.80	—
Isolation	500 MHz - 2.0 GHz	dB	45	47	—
	2.0 - 3.0 GHz	dB	—	33	—
VSWR	0.25 - 3.0 GHz	Ratio	—	1.2:1	—
P1dB	500 MHz - 2.0 GHz, $V_C = 3 \text{ V}$	dBm	—	20	—
P1dB	500 MHz - 2.0 GHz, $V_C = 5 \text{ V}$	dBm	—	28	—
IP2	2 Tone, 900 MHz, 5 MHz Spacing, $V_C = 3 \text{ V}$	dBm	—	85	—
IP3	2 Tone, 900 MHz, 5 MHz Spacing, $V_C = 3 \text{ V}$	dBm	—	50	—
Ton, Toff	50% Control to 90% RF, 50% Control to 10% RF	nS	—	20	—
Trise, Tfall	10% to 90% RF, 90% to 10% RF	nS	—	10	—
Transients	In-band	mV	—	15	—
Control Current	$ V_C = 3.0 \text{ V}$	μA	—	5	20

Lead-Free MSOP-10[†]

[†] Reference Application Note M538 for lead-free solder reflow recommendations.

Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

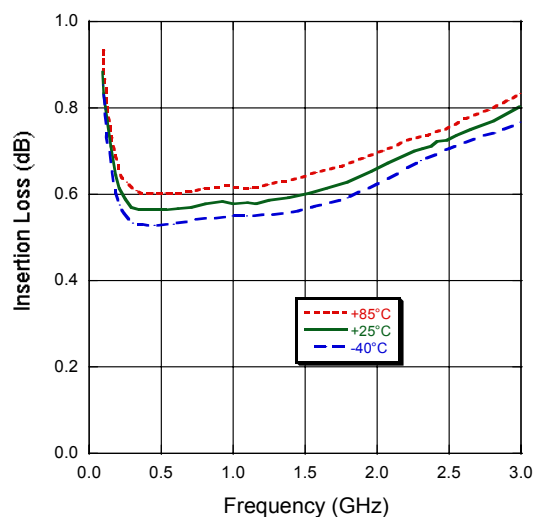
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

**GaAs High Isolation Switch
DC - 3.0 GHz**

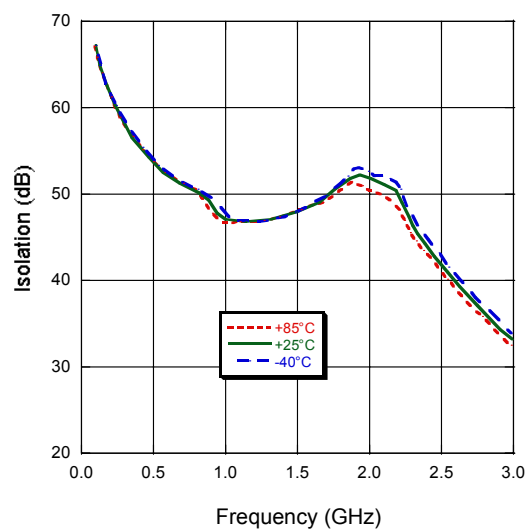
**MASWSS0169
V2**

Typical Performance Curves

Insertion Loss



Isolation



VSWR

